Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Extended temperature range T_i = 175 °C
- · Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	4.2	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 4.2 \text{ A}; T_j = 25 \text{ °C}$		-	32	43	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D I
2	D	drain		
3	G	gate	0 1 1 2 13	G—(FA)
4	S	source	SC-74; TSOP6 (SOT457)	s
5	D	drain		017aaa253
6	D	drain		

6. Ordering information

Table 3. Ordering information

Type number Package						
	Name	Description	Version			
PMN40ENA	SC-74; TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN40ENA	3N

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	4.2	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	3	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	17	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	652	mW
			[1]	-	1.7	W
		T _{sp} = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source Drain	Diode				•	
Is	source current	T _{amb} = 25 °C	[1]	-	1.7	Α
ESD maximu	m rating				•	
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	500	V
Avalanche ru	iggedness	,	,	'		,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.75 A; DUT in avalanche (unclamped)		-	24	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

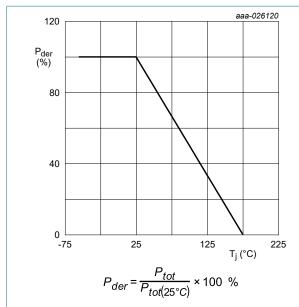
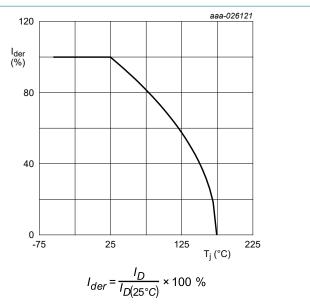


Fig. 1. Normalized total power dissipation as a function of junction temperature



ig. 2. Normalized continuous drain current as a function of junction temperature

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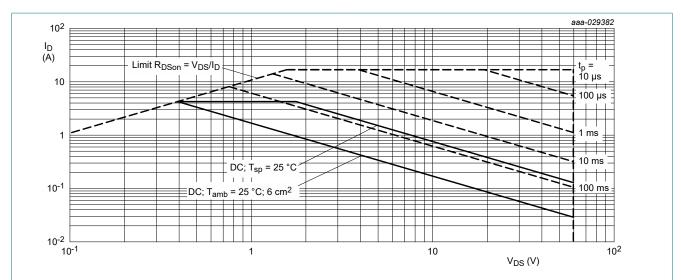


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

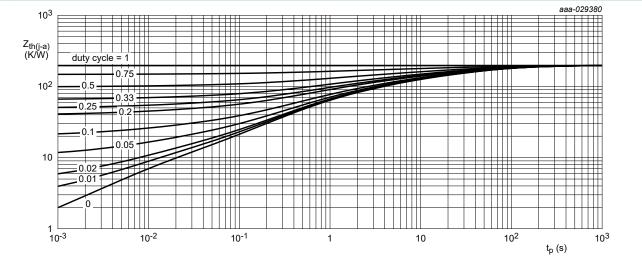
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	200	230	K/W
junction to am	junction to ambient		[2]	-	78	90	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 (PCB), single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

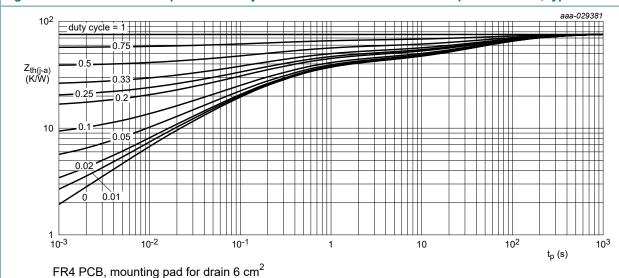


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.3	1.7	2.7	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 4.2 A; T _j = 25 °C	-	32	43	mΩ
resistance	resistance	V _{GS} = 10 V; I _D = 4.2 A; T _j = 175 °C	-	69	93	mΩ
	$V_{GS} = 4.5 \text{ V}; I_D = 3.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	38	53	mΩ	
9fs	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 4.2 \text{ A}; T_j = 25 \text{ °C}$	-	5	-	S
R_G	gate resistance	f = 1 MHz	-	3.5	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 4.2 \text{ A}; V_{GS} = 10 \text{ V};$	-	10	15	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.7	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	590	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	60	-	pF
C _{rss}	reverse transfer capacitance	_	-	34	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; I_D = 4.2 \text{ A}; V_{GS} = 10 \text{ V};$	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	5	-	ns
t _{d(off)}	turn-off delay time	1	-	11	-	ns
t _f	fall time	1	-	4	-	ns
Source-drai	in diode	•			<u> </u>	
V_{SD}	source-drain voltage	I _S = 1.7 A; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 2.3 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	15.5	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	_	8.3	-	nC

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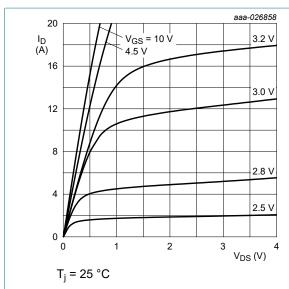


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

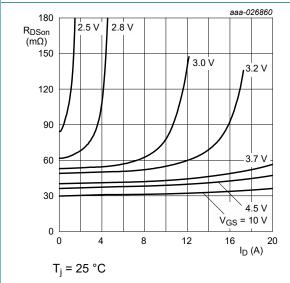


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

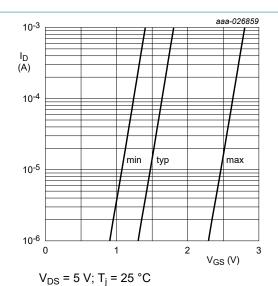


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

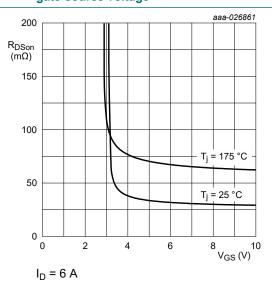


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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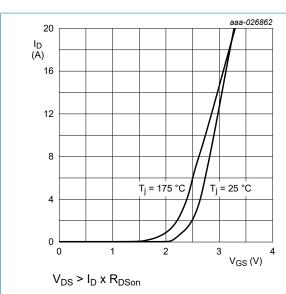


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

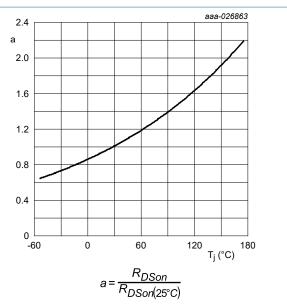


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

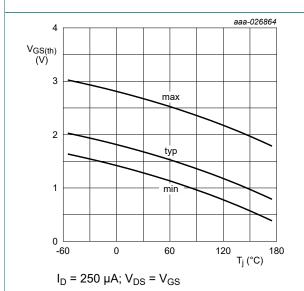


Fig. 12. Gate-source threshold voltage as a function of junction temperature

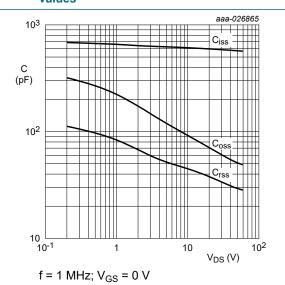


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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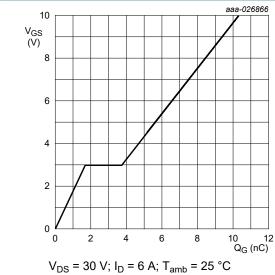


Fig. 14. Gate-source voltage as a function of gate charge; typical values

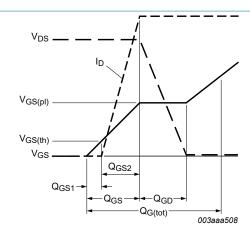


Fig. 15. Gate charge waveform definitions

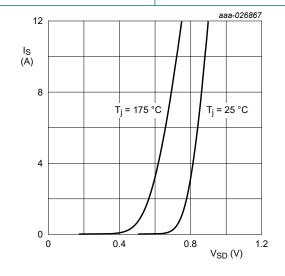
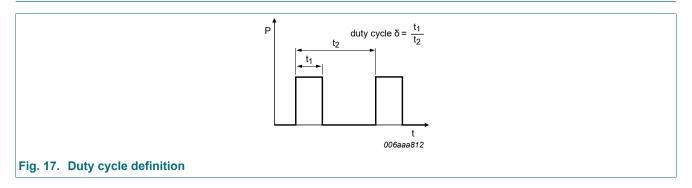


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information



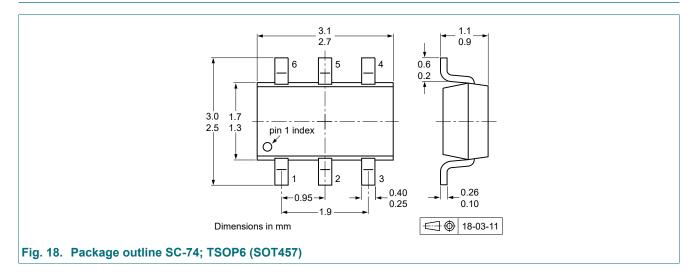
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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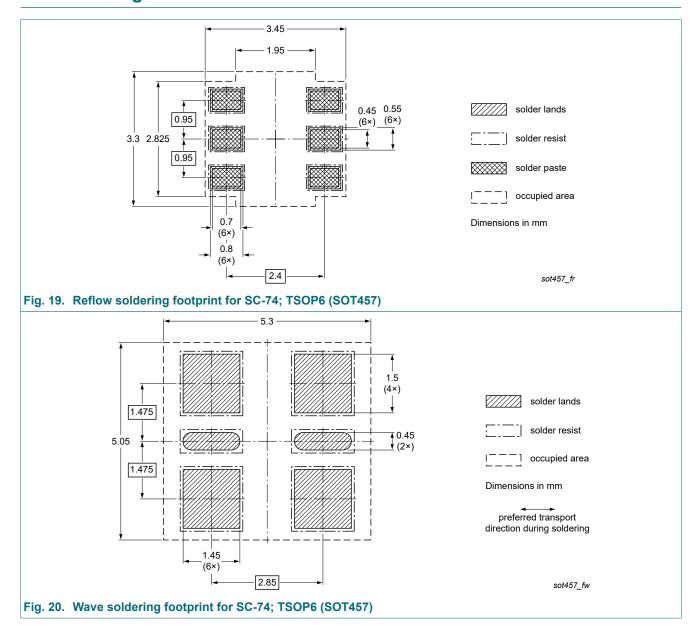
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN40ENA v.1	20190411	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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